

For more information please contact:

Prof. Alexander E. Yunovich

Phone: +7 (095) 939-29-94;

Fax: +7(095) 939-37-31;

E-mail: yunovich@sconyuno.phys.msu.su.

Dr. Wsevolod V. Lundin

Phone +7 (812) 247-91-24

Fax +7 (812) 247-86-40

E-mail: lundin.vpeggroup@mail.ioffe.ru

Organising Committee

P.S.Kop'ev	Chair	Ioffe Institute, RAS
A.E.Yunovich	Vice Chair	Moscow State University
W.V.Lundin	Secretary	Ioffe Institute, RAS
A.N.Turkin	Secretary	Moscow State University Corvette-Lights
V.S.Abramov		UniSapph
S.P.Chernyh		TDI Inc.
V.A.Dmitriev		Ioffe Institute, RAS
A.E.Nikolaev		Ioffe Institute, RAS
A.V.Sakharov		Ioffe Institute, RAS
E.E.Zavarin		St.Petersburg State Polytechnical University
V.G.Sidorov		

Program Committee

P.S.Kop'ev	Chair	Ioffe Institute, RAS
N.N.Ledentsov		TU Berlin
M.G.Mil'vidskii		State Institute of Rare Metals
A.S.Usikov		Ioffe Institute, RAS
V.M.Ustinov		Ioffe Institute, RAS
Dr. V.G.Mokerov		Institute of Radioengineering and Electronics, RAS
S.Yu.Shapoval		Institute of Solid State Physics in Chernogolovka, RAS
A.N.Kovalev		Moscow Institute of Steel and Alloys

2nd Russian Conference “Gallium, Aluminum and Indium Nitrides”



**Ioffe Institute of the Russian Academy of Science, St. Petersburg, February 3-4, 2003
1st Announcement and Call for Papers**

General Information

The annual Russian Conference on Gallium, Aluminum and Indium Nitrides organized for the first time in 1997 as a workshop aims to bring together scientific groups working in the field of III-nitrides in Russia. Despite the national character of the Russian III-N conference series, participants from all over the world are invited to attend.

Organization and Location

III-N 2003 will be held in the Scientific and Educational Center of Ioffe Institute, five minutes walk from the main building of Ioffe Institute.

Format of the Conference

The 2nd Russian Conference “Gallium, Aluminum and Indium Nitrides” will be held in St. Petersburg at the Ioffe Institute on February 3-4, 2003. All contributed papers will be presented in poster sessions with 5-minute oral introductions, while the backbone of the meeting will consist in invited oral presentations. The official language of III-N 2003 is Russian but some presentations may be done in English.

Scope of the Conference

- Substrates for the epitaxial growth of III-N.
- Bulk growth.
- Epitaxial growth
- Narrow-Band-Gap and Diluted nitrides.
- Optical, electronic and structural properties of III-N materials.
- Properties of quantum-size heterostructures based on III-N.
- Devices: growth and processing.
- Application of III-N based electronic and optoelectronic devices.

Exhibition & sponsorship

Potential exhibitors are invited to participate in the conference industrial exhibition.

Opportunities to sponsor the conference are also welcome.

Interested companies are requested to contact the organizing committee chairman as soon as possible.

Preliminary registration and visa support

To get a preliminary registration and visa support foreign participants must contact to the Organizing Comity by e-mail: lundin.vpegroup@mail.ioffe.ru as soon as possible.

Submission

Short abstracts in English (100 words) as well as extended abstracts (desirable in Russian, but acceptably in English for foreign participants) must be submitted electronically prior to December 15, 2002 as a file attached to an e-mail to:

lundin.vpegroup@mail.ioffe.ru.

Abstracts will be published prior to the Conference.

Guidelines for Abstract preparation

Extended abstracts of two pages length must be prepared in MS Word for Windows 95/97 or 2000 format. Page size must be 210*297 mm (A4) with 2.54 cm top, bottom and right margins and 3.17 cm left margin. Use 12 pt. Times New Roman font for the whole document. Title, authors, and affiliations must be centered. Please, indicate e-mail address of corresponding author. Presenting author – underlined.

Main text – with single spacing, justified. References – in the end of the abstract.

Figures must be black-and-white, pasted in the abstract text.